

#### **CT Micro**

#### **Features**

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Temperature range 55 °C to 100 °C

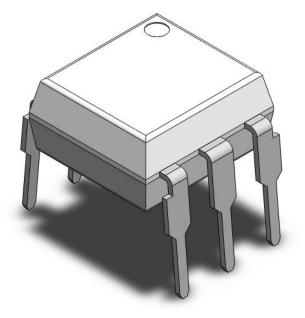
### **Applications**

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

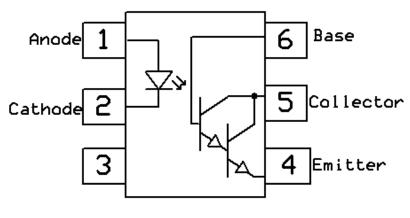
#### **Description**

The 4N2X, 4N3X, H11BX and TIL113 series consists of a photo darlington optically coupled to a gallium arsenide Infrared-emitting diode in a 6-lead DIP package with bending options.

### **Package Outline**



### **Schematic**



Note: Different bending options available. See package dimension.



Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	V <sub>RMS</sub>	
Topr	Operating temperature	-55 ~ +100	°C	
Тѕтс	Storage temperature	-55 ~ +125	°C	
TsoL	Soldering temperature	260	°C	
Emitter		·	<u> </u>	
l <sub>F</sub>	Forward current	60	mA	
I <sub>F</sub> (TRANS)	Peak transient current (≤1µs P.W,300pps)	1	А	
V <sub>R</sub>	Reverse voltage	6	V	
PD	Power dissipation	100	mW	
Detector		·	<u> </u>	
PD	Power dissipation	150	mW	
Bvceo	Collector-Emitter Breakdown Voltage	55	V	
Вусво	Collector-Base Breakdown Voltage	55	V	
B <sub>VECO</sub>	Emitter-Collector Breakdown Voltage	7	V	
B <sub>VEBO</sub>	Emitter-Base Breakdown Voltage	7	V	



### **Electrical Characteristics** $T_A = 25$ °C (unless otherwise specified)

#### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I <sub>F</sub> =10mA		1.2	1.7	V	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 6V	-	-	5	μΑ	
Cin	Input Capacitance	f= 1MHz	-	45	-	pF	

#### **Detector Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B <sub>VCEO</sub>	B <sub>VCEO</sub> Collector-Emitter Breakdown I <sub>C</sub> = 100μA		55	-	-	V	
Bveco	Emitter-Collector Breakdown	I <sub>E</sub> = 1mA	7	-	-	V	
Вусво	Collector-Base Breakdown	I <sub>C</sub> = 100μA	55	-	-	V	
ICEO	Collector-Emitter Dark Current	V <sub>CE</sub> = 10V, I <sub>F</sub> =0mA	-	-	50	nA	

#### **Transfer Characteristics**

Symbol	P	arameters	Test Conditions	Min	Тур	Max	Units	Notes
		4N29, 4N30		100	-	-		
		4N31	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V	50	-	-		
	0	4N32, 4N33		500	-	-		
CTD	Current	H11B1		500	-	-	0/	
CTR	Transfer	H11B2	I <sub>F</sub> = 1mA, V <sub>CE</sub> = 10V	200	-	-	%	
	Ratio	H11B3	]	100	-	-		
		H11B255	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 5V	100	-	-		
		TIL113	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 1V	300	-	-		
	Collector- Emitter	4N29, 4N30, 4N32, 4N33	I <sub>F</sub> = 8mA, I <sub>C</sub> = 2mA	-	-	1.0		
.,	Saturation	4N31, TIL113	I <sub>F</sub> = 8mA, I <sub>C</sub> = 2mA	-	-	1.2	.,	
VCE(SAT)	V <sub>CE(SAT)</sub> Voltage	H11B1, H11B2, H11B3	I <sub>F</sub> = 1mA, I <sub>C</sub> = 1mA	-	-	1.0	V	
		H11B255	I <sub>F</sub> =50mA, I <sub>C</sub> = 50mA	-	-	1.0		
Rio	Isolation Resistance		V <sub>IO</sub> = 500V <sub>DC</sub>	1x10 <sup>11</sup>			Ω	
C <sub>IO</sub>	Isolation Capacitance		f= 1Mhz		0.25		pF	

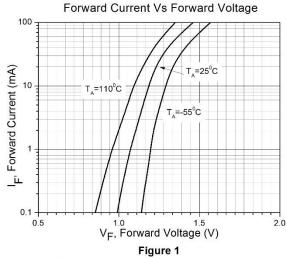


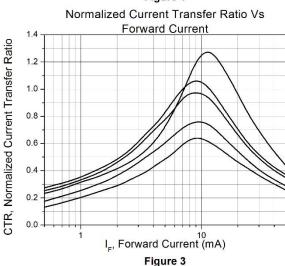
### **Switching Characteristics**

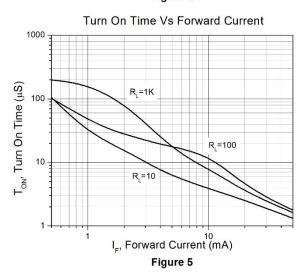
Symbol	Para	ameters	Test Conditions	Min	Тур	Мах	Units	Notes
	Turn On Time	4N2X, 4N3X,	I <sub>F</sub> = 200mA, I <sub>c</sub> = 50mA, R <sub>L</sub> =	-	-	4.7	- µs	
T		TIL113	100Ω					
T <sub>ON</sub>		LI11DV	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V, R <sub>L</sub> =		24			
		H11BX 100Ω -	-	24	-			
	Turn Off Time	4N29, 4N30,				20		
		4N31	I <sub>F</sub> = 200mA, I <sub>c</sub> = 50mA, R <sub>L</sub> =	-	-	30		
T		4N32, 4N33,	100Ω			00	<b>]</b>	
Toff		TIL113		-	-	90	μs	
		H11BX	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V, R <sub>L</sub> =		17	17 -		
		ППВА	100Ω	-	''			

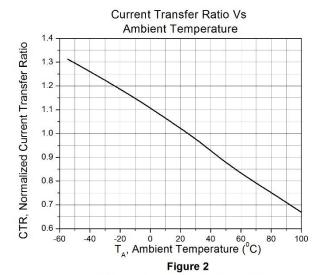


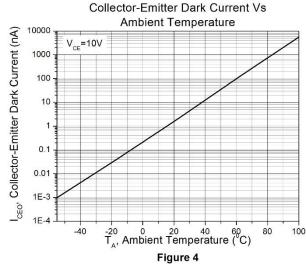
### **Typical Characteristic Curves**

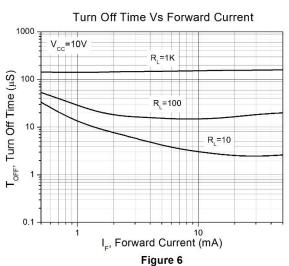








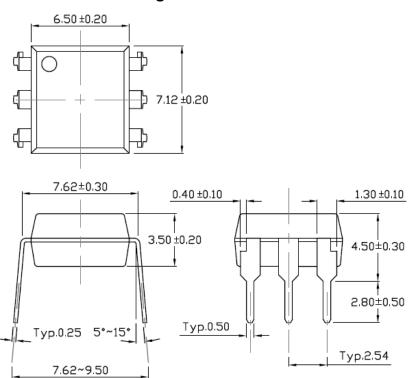




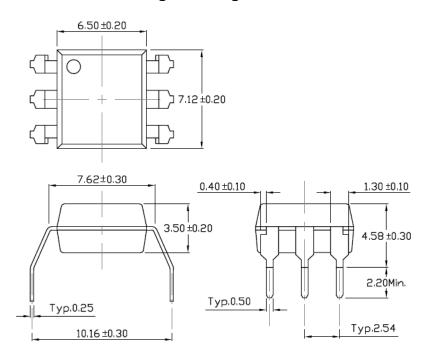


## Package Dimension Dimensions in mm unless otherwise stated

#### Standard DIP - Through Hole

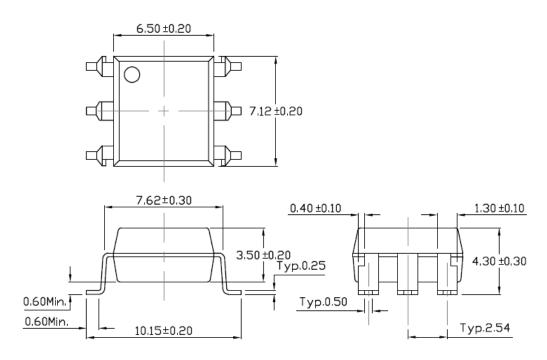


### Wide Lead Forming - Through Hole

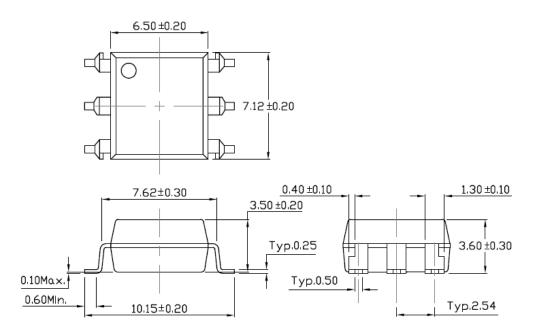




#### **Surface Mount Forming**

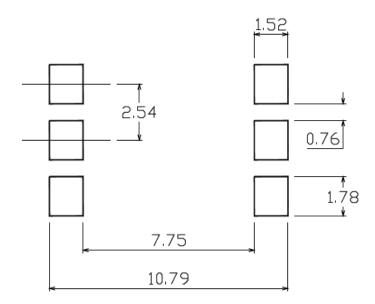


### **Surface Mount Forming (Low Profile)**

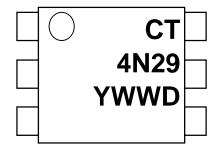




### Recommended Solder Mask Dimensions in mm unless otherwise stated



## **Marking Information**



#### Note:

CT: Logo

4N29 : Product Number

Y : Fiscal Year WW : Work Week

D : Production Code



### **Ordering Information**

4N2X(Y)(Z)-G, 4N3X(Y)(Z)-G, H11BX(Y)(Z)-G

X = Part. No. (9 for 4N2X), (0,1,2,3 for 4N3X series), (1,2,3,255 for H11BX series)

Y = Lead form option (S, SL, M or none)

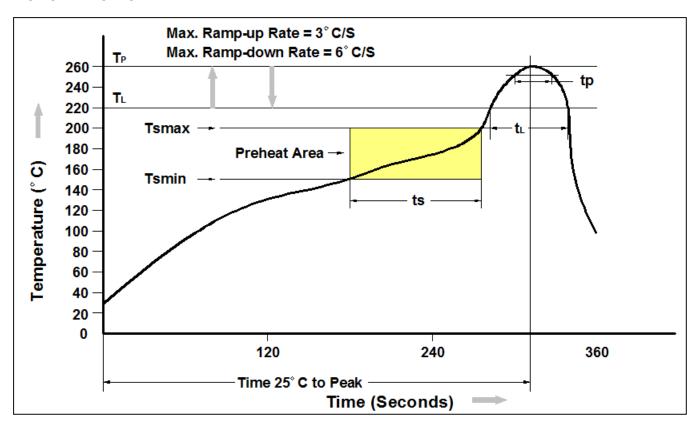
Z = Tape and reel option (TA, TB or none)

G= Material option (G: Green, None: Non-green)

Option	Description	Quantity	
None	None Standard 6 Pin Dip		
М	M Wide Lead Forming		
S(TA)	S(TA) Surface Mount Lead Forming – With Option A Taping		
S(TB)	S(TB) Surface Mount Lead Forming – With Option B Taping		
SL(TA)	SL(TA) Surface Mount Lead Forming(Low Profile) – With Option A Taping		
SL(TB)	1000 Units/Reel		



#### **Reflow Profile**



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t⊳)	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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